

Ref #	Hits	Search Query	DBs	Default Operat or	Plural s	Time Stamp
L1	1946	(pressure adj sensor) with (porous porosity bubble cavity void microporous nanoporous)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/12/13 13:07
L2	250	1 and ((pressure adj sensor) with semiconductor)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/12/13 13:01
L3	17	2 and (parallel perpendicular\$2) with (porous porosity bubble cavity void microporous nanoporous)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/12/13 12:57
L4	2	2 and (parallel perpendicular\$2) with ((porous porosity bubble cavity void microporous nanoporous) near3 silicon)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/12/13 12:58
L5	1751	1 and ((pressure adj sensor) with (hollow cavity))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/12/13 13:01
L6	701	5 and layer	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/12/13 13:02
L7	452	6 and silicon	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/12/13 13:03
L8	420	7 and first	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/12/13 13:05
L9	404	8 and second	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/12/13 13:05
L10	95	9 and (structure near3 (porous porosity bubble cavity void microporous nanoporous))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/12/13 13:08
L11	1	10/655,839	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/12/13 16.34

S1	0	(10/655839).CCLS.	US-PGPU B; USPAT; EPO; JPO	OR	OFF	2004/12/13 07:30
S2	1	10/655839	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/12/13 12:07
S3	1	"20040029359"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/12/13 08:36
S4	1	"20040029359"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/12/13 08:39